1. General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540X

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

3. Applications

- · Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch mode power supply

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-400	V
I _C	collector current			-	-	-0.5	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-	-1	Α
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -20 mA; T_{amb} = 25 °C		140	-	450	
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -200 mA; I_{B} = -40 mA; T_{amb} = 25 °C	[1]	-	-	2000	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



400 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		C
2	С	collector		В—
3	В	base	3 2 1	- N
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

	Type number	Package					
		Name	Description	Version			
	PBHV9540X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV9540X	%4H

[1] % = placeholder for manufacturing site code

400 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor

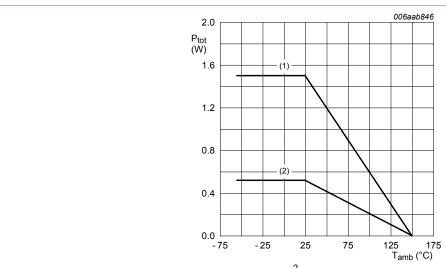
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-400	V
V_{CEO}	collector-emitter voltage	open base		-	-400	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-400	V
V_{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-0.5	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-1	Α
I _B	base current			-	-250	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.52	W
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	240	K/W
			[2]	-	_	83	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

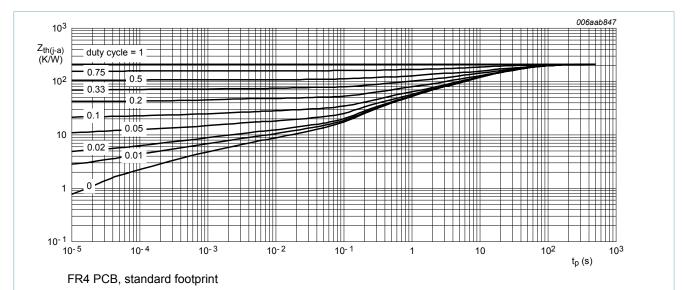


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

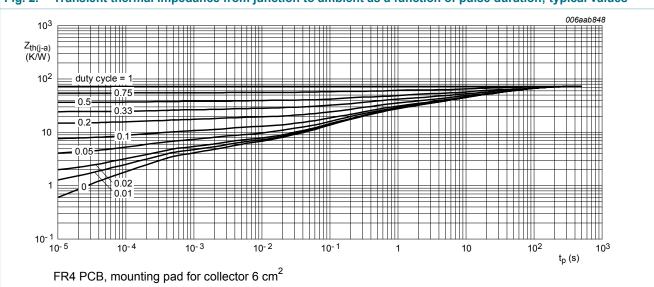


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

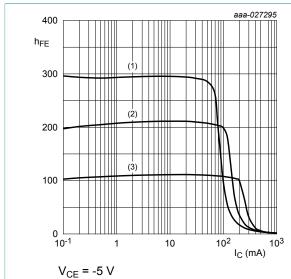
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		-400	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_C = -2.5 mA; I_B = 0 A; T_{amb} = 25 °C		-400	-	-	V
V _{(BR)CES}	collector-emitter breakdown voltage (base shorted)	I_C = -2.5 mA; V_{BE} = 0 V; T_{amb} = 25 °C		-400	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_E = -100 \mu A; I_C = 0 A; T_{amb} = 25 °C$		-7	-	-	V
I _{CBO}	collector-base cut-off	V_{CB} = -320 V; I_{E} = 0 A; T_{amb} = 25 °C		-	-	-100	nA
	current	V _{CB} = -320 V; I _E = 0 A; T _j = 150 °C		-	-	-10	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -320 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -7 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -20 mA; T_{amb} = 25 °C		140	-	450	
		V_{CE} = -5 V; I_{C} = -100 mA; T_{amb} = 25 °C	[1]	140	-	400	
V _{CEsat}	collector-emitter saturation voltage	I_C = -100 mA; I_B = -20 mA; T_{amb} = 25 °C	[1]	-	-	-250	mV
		$I_C = -200 \text{ mA}; I_B = -40 \text{ mA};$	[1]	-	-	-400	mV
R _{CEsat}	collector-emitter saturation resistance	T _{amb} = 25 °C	[1]	-	-	2000	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = -100 mA; I_B = -10 mA; T_{amb} = 25 °C	[1]	-	-	-0.9	V
		I_C = -200 mA; I_B = -40 mA; T_{amb} = 25 °C	[1]	-	-	-1	V
V_{BE}	base-emitter voltage	V_{CE} = -10 V; I_{C} = -200 mA; T_{amb} = 25 °C	[1]	-	-	-0.9	V
t _d	delay time	$V_{CC} = -6.2 \text{ V}; I_C = -100 \text{ mA};$		-	60	-	ns
t _r	rise time	I_{Bon} = -10 mA; I_{Boff} = 20 mA; T_{amb} = 25 °C		-	3650	-	ns
t _{on}	turn-on time	- anno 100		-	3710	-	ns
t _s	storage time			-	810	-	ns
t _f	fall time			-	900	-	ns
t _{off}	turn-off time			-	1710	-	ns
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C		-	65	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	14	-	pF

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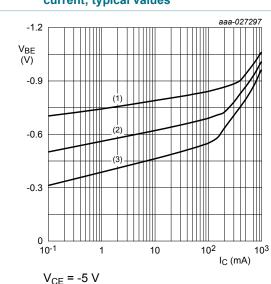
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f_{c} = 1 MHz; f_{amb} = 25 °C	-	235	-	pF

[1] Pulse test: $t_0 \le 300 \,\mu\text{s}$; $\delta \le 0.02$



(1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -55 \,^{\circ}C$

Fig. 4. DC current gain as a function of collector current; typical values



(1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C Fig. 6. Base-emitter voltage as a function of collector

current; typical values

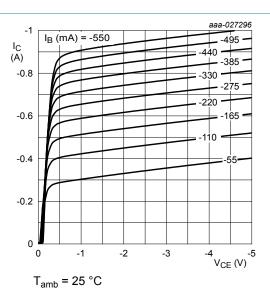
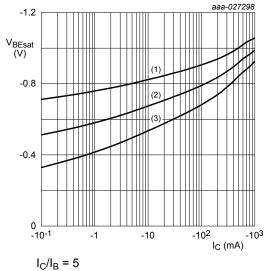


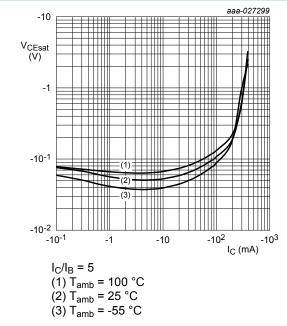
Fig. 5. Collector current as a function of collectoremitter voltage; typical values



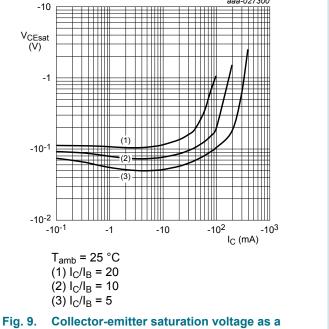
 $I_C/I_B = 5$ (1) $T_{amb} = -55 ^{\circ}C$ (2) $T_{amb} = 25 ^{\circ}C$ (3) $T_{amb} = 100 ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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Collector-emitter saturation voltage as a Fig. 8. function of collector current; typical values



function of collector current; typical values

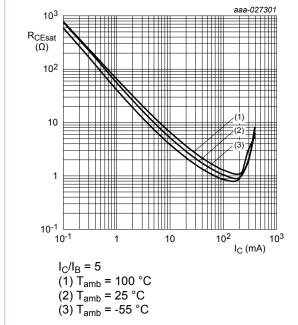


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

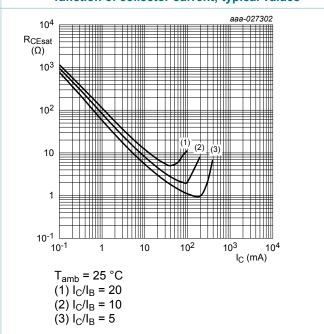
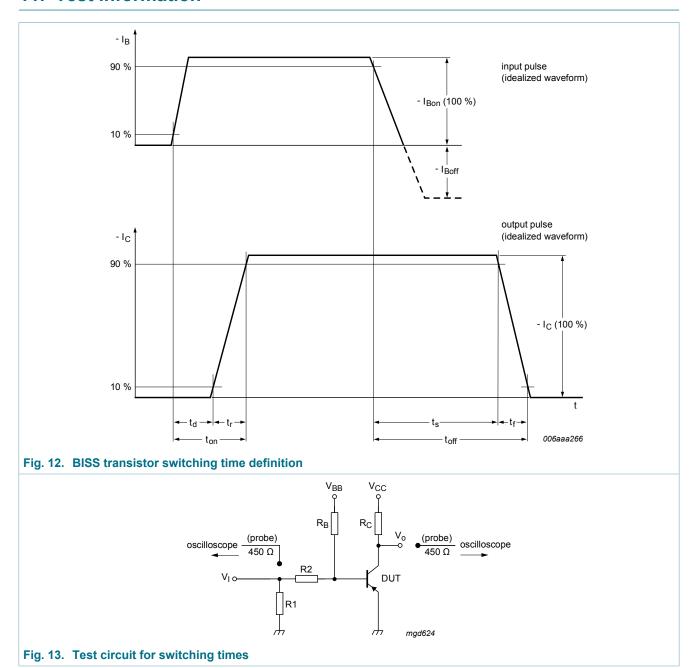


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

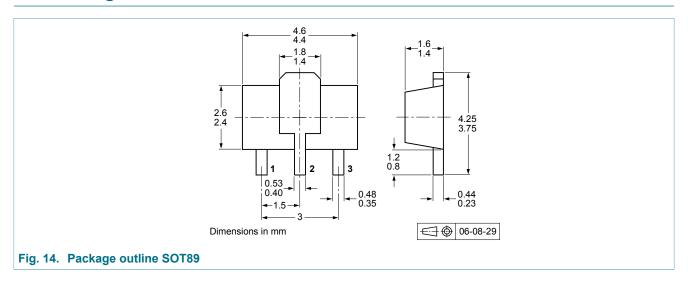


Quality information

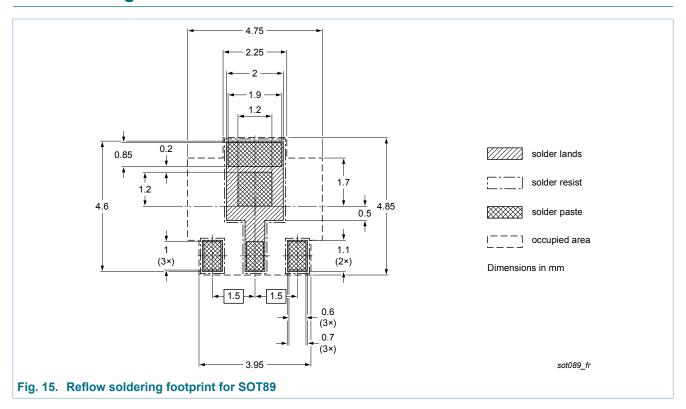
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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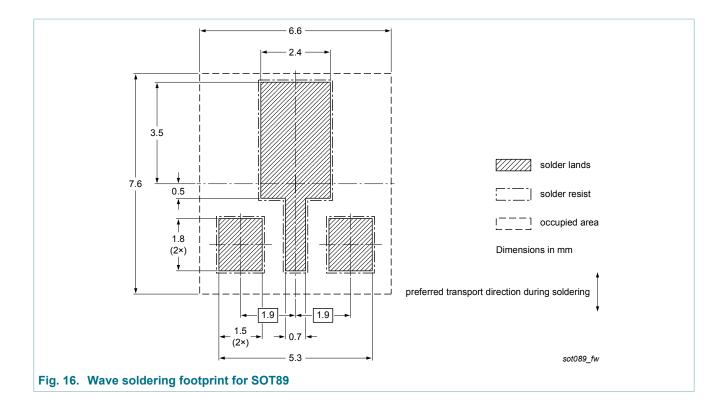
12. Package outline



13. Soldering



400 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9540X v.1	20170928	Product data sheet	-	-

400 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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	Features and benefits

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